NSN 5961-01-500-9655

No Fiig: A110a0

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-500-9655 **Inclosure Material:** Metal **Overall Length:** 0.948 inches **End Application:** C-17a aircraft **Mounting Facility Quantity: Electrode Internally-electrically Connected To Case:** Cathode **Mounting Method:** Threaded stud **Overall Width Across Flats:** 0.437 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 45.0 repetitive peak reverse voltage, peak total value and 54.0 nonrepetitive peak reverse voltage and 45.0 working peak reverse voltage **Current Rating Per Characteristic:** 25.00 amperes source cutoff current absolute and 600.00 amperes forward current, average preset **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Special Features:** Request name semiconductor, diode schottky barrier fast recovery, this item is selected from jantx1n6391 to bealtered for size **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:**